PCN Number: 20			202	201217001.2B PC					PCI	CN Date: Mar 18, 2021			1
Tit	le:	Quali	ification of RF	AB as an additional Fab site option for select LBC7 devices									
Customer Contact:					PCN Manager				De	pt:		Quality Services	
					Jul 25, 2021			Estima	ited	San	nple	Date provided at	
Proposed 1 st Ship Date:					25, 202	1		Availa	bilit	y:		sample request.	
Ch	ange Ty	_								ı			
Щ	Assembly Site				Assembly Process					Assembly Materials			
Ш	Design				Electrical Specification							anical Specific	ation
Test Site			Packing/Shipping/ Wafer Bump Mate					<u> </u>		Process			
	Wafer Bump Site✓ Wafer Fab Site			\square			Materials Materials			\square		r Bump Proces	SS
	water	rau S	oite	$\frac{\square}{\square}$			r chang				ware	r Fab Process	
					•		Detai						
De	scrintic	n of (Change:			PCIN	Detai	15					
				on t	o the D	escri	intion o	f Char	nge	sect	ion as	shown belo	w.
							-		_			n of a PI Lay	
	rt of thi				, 011011		g						<u> </u>
•													
												ation facility as	s an
ado	ditional \	Wafer	Fab source fo	r the	selecte	d dev	ices list	ed in "	Prod	uct A	Affecte	d" section.	
											1 011		1
			Current Site						_		al Site		
С	urrent Site	Fab	Process		Wafer Diamete		Addit			Proc	ess	Wafer Diameter	
	FFAB		LBC7		200mm	า	RFA	λB		LB	C7	300mm]
			Current Top L	ayer	Materia	<mark>ıl</mark>	Nev	v Top L			erial		
			Current Top L BOAC (<mark>il</mark>	Nev		.ayeı AC +		erial		
			BOAC (No P	I)						erial		
		s are p	BOAC (No P	I)						erial		
	al detail ason fo	s are p	BOAC (No P	I)						cerial		
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Cor	ason fontinuity	s are por Cha	BOAC (provided in the nge: pply	No P	I) al Data	Section	on.	BOA	AC +	PI		ive / negativ	/e):
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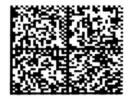
Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS MADE IN: Malaysia 2DC: 20:

MSL 2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04

OPT: ITEM:

(L)T0:3750



(1P) SN74LS07NSR (P) 0336 31T)LOT: 3959047MLA 4W) TKY(1T) 7523483S12 (P) (2P)

(2b) REV: (V) 0033317 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

Product Affected:

UCC27524A1QDGNRQ1

UCC27524AQDGNRQ1

UCC27524AQDRQ1

Automotive Qualification Summary

(As per AEC-Q100 and JEDEC Guidelines)

UCC27524A1QDGNRQ1 and UCC27524AQDRQ1 FFAB to RFAB

Approve Date 22-October-2020

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

							nopia) ca ac. Hamber					
Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: UCC27524A1QDGNRQ1	Qual Device: UCC27524AQDRQ1	Process QBS Reference TPS2543QRTE	Product QB S Reference UCC27524AQDRQ1	Package QBS Reference PGA308AQDGSRQ1	Package QBS Reference UCC27524
Test Group	A – Ad	celerated Environ	ment S	tress T	ests							
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST, 130C/85%RH	96 Hours	-	-	3/231/0	1/77/0	3/231/0	3/231/0
AC	А3	JEDEC JESD22-A102	3	77	Autoclave 121C	96 Hours	-	-	3/231/0	1/77/0	3/231/0	-
uHAST	А3	JEDEC JESD22-A102	3	77	unBiased HAST, 130C/85%RH	96 Hours	-	1/77/0	-	-	-	3/231/0
тс	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle, - 65/150C	500 Cycles	-	1/77/0	3/231/0	1/77/0	3/231/0	3/231/0
PTC	A5	JEDEC JESD22-A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	N/A	N/A	N/A	N/A	N/A
HTSL	A6	JEDEC JESD22-A103	1	45	High Temp. Storage Bake, 175C	500 Hours	-	1/45/0	1/45/0	1/45/0	1/45/0	3/231/0
Test Group	Test Group B – Accelerated Lifetime Simulation Tests											
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 150C	408 Hours	-	-	3/231/0		3/231/0	-
HTOL	B1	JEDEC JESD22-A108	3	77	Life Test, 140C	480 Hours	-	-	-	2/154/0	-	-
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	-	3/2640/0	1/800/0	3/2400/0	-
EDR	В3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	1	N/A	N/A	N/A	N/A	3/231/0	-
Test Group	C – Pa	ickage Assembly I	ntegrity	/ Tests								
WBS	C1	AEC Q100-001	1	30	Bond Shear (Cpk>1.67)	Wires	1/30/0	1/30/0	-	-	-	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull (Cpk>1.67)	Wires	1/30/0	1/30/0	-	-	-	3/90/0
SD	C3	JEDEC JESD22-B102	1	15	Solderability (>95% Lead Coverage)	Pb & Pb-Free	-	-	1/15/0	-	-	-
PD	C4	JEDEC JESD22-B100 and B108	3	10	Physical Dimensions (Cpk>1.67)	1	-	-	3/30/0	-	-	3/30/0

Test Grou	p D – D	ie Fabrication Reli	ability 1	ests								
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology
							Requirements	Requirements	Requirements	Requirements	Requirements	Requirements
TDDB	D2	JESD35	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	
							Requirements	Requirements	Requirements	Requirements	Requirements	Requirements
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature	-	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology	Completed Per Process Technology
					Instability		Requirements	Requirements	Requirements	Requirements	Requirements	Requirements
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Grou	p E – E	lectrical Verificatio	n Tests									
HBM	E2	AEC Q100-002	1	3	ESD - HBM	4000 V	1/3/0	1/3/0	-	-	-	
CDM	E3	AEC Q100-011	1	3	ESD - CDM	1000 V	1/3/0	1/3/0	-	-	-	
LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC Q100-004)	1/6/0	1/6/0	1/6/0	-	-	-
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, Hot, & Cold Test	3/90/0	3/90/0	3/90/0	3/90/0	-	-

Qual Device UCC27524A1QDGNRQ1 is qualified at LEVEL2-260C Qual Device UCC27524AQDRQ1 is qualified at LEVEL1-260C

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Performed for Iris, Jassed HASI, AU, BHASI, TC & PTC sample Ambient Operating Temperature by Automotive Grade Level: Grade 0 (or E): -40°C to +150°C Grade 1 (or C): -40°C to +155°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level): Room/Hot/Cold : HTOL, ED

Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU Room: AC/uHAST

Green/Pb-free Status: Qualified Pb-Free(SMT) and Green

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